Electronic Supplementary Material (ESI) for Journal of Materials Chemistry A.

Supporting Information

Large dielectric constant, high acceptor density, and deep electron traps in perovskite solar cell material $CsGeI_3$

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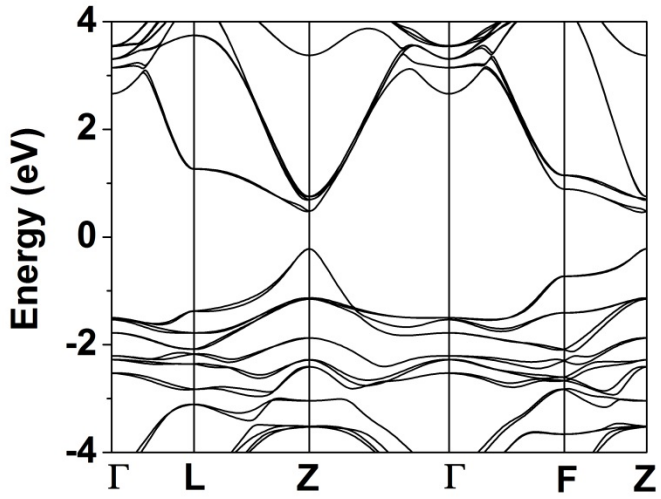

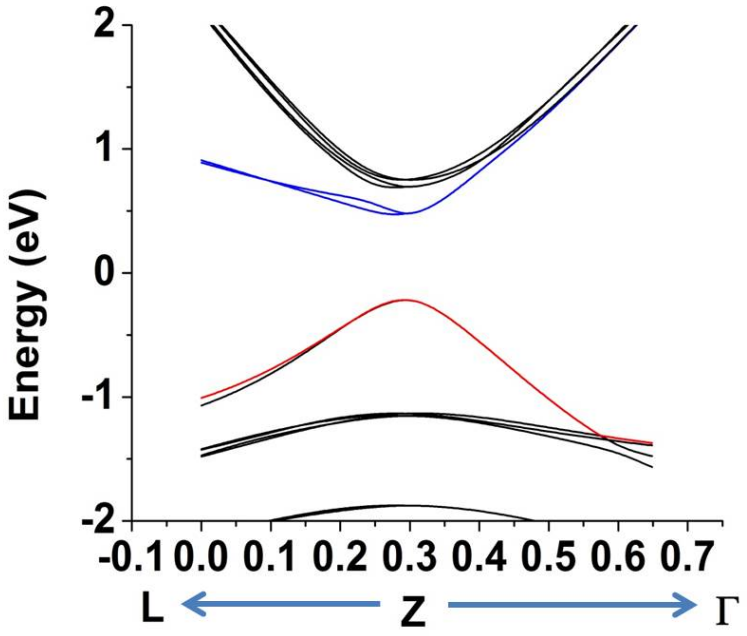

The top panel shows that band structure of $CsGeI_3$; the bottom panel is the band structure zoomed in near the Z point. The band structure is calculated using the PBE functionals including the spin-orbit coupling.